

1 AMP FAST RECOVERY SILICON RECTIFIERS BA157 THRU BA159

TECHNICAL SPECIFICATION

FEATURES

- Fast recovery times for high efficiency
- Low cost construction utilizing void - free moulded plastic technique
- Plastic package has Underwriters Laboratories Flammability Classification 94V-0
- High surge current capability
Low leakage
- High temperature soldering capability
250°C/10 seconds/9.5mm (.375in.) lead length at 2.3kg (5lb) tension
- Easily cleaned with Freon, Alcohol, Chlorothene and other similar solvents

MECHANICAL DATA

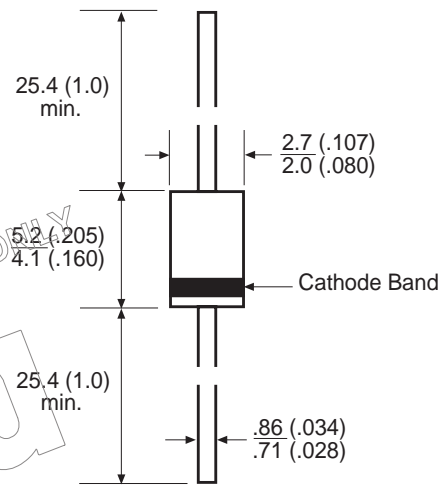
Case : JEDEC DO-41, moulded plastic.
 Terminals : Plated axial leads, solderable per MIL-STD-202, Method 208.
 Polarity : Colour band denotes cathode end.
 Mounting Position : Any
 Weight : 0.3 grams (0.012 ounce)

VOLTAGE
400 to 1000 Volts

CURRENT
1.0 Amp

DIMENSIONS - millimeters (inches)

DO-41



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

	Symbols	BA157	BA158	BA159	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	400	600	1000	V
Maximum RMS Voltage	V_{RMS}	280	420	700	V
Maximum DC Blocking Voltage	V_{DC}	400	600	1000	V
Maximum Average Forward Rectified Current 9.5mm (.375in.) Lead Length at $T_A = 75^\circ\text{C}$	$I_{F(AV)}$	1.0			A
Peak Forward Surge Current, 8.3 ms single half sine - wave superimposed on rated load	I_{FSM}	30			A
Maximum Instantaneous Forward Voltage at 1.0A	V_F	1.2			V
Maximum Reverse Current at Rated DC Blocking Voltage	I_R	$T_A = 25^\circ\text{C}$	5.0		μA
		$T_A = 100^\circ\text{C}$	100		μA
Maximum Reverse Recovery Time (see Note 3)	t_{rr}	150	250	500	nS
Typical Junction Capacitance (see Note 1)	C_J	15			pF
Typical Thermal Resistance (see Note 2)	R_{THja}	50			$^\circ\text{C/W}$
Operating Temperature Range	T_J	- 50 to + 175			$^\circ\text{C}$
Storage Temperature Range	T_{STG}	- 50 to + 175			$^\circ\text{C}$

Notes :

1. Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts
2. Thermal Resistance from Junction to Ambient
3. Test Conditions : $I_F = 0.5\text{A}$, $I_R = 1.0\text{A}$ recovery to 0.25A

RATING AND CHARACTERISTIC CURVES

FIG. 1 - FORWARD CURRENT DERATING CURVE

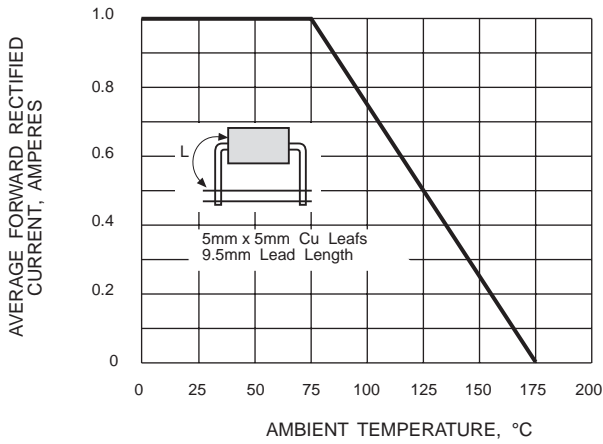


FIG. 2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

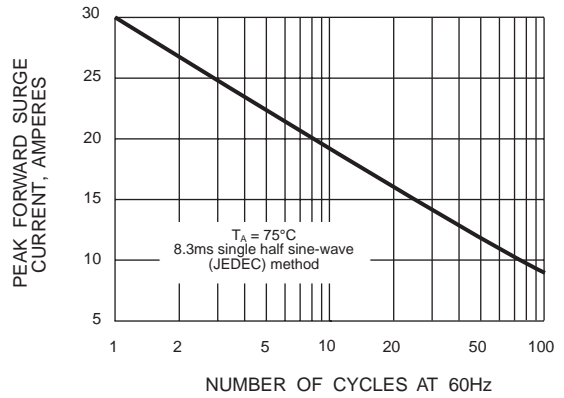


FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

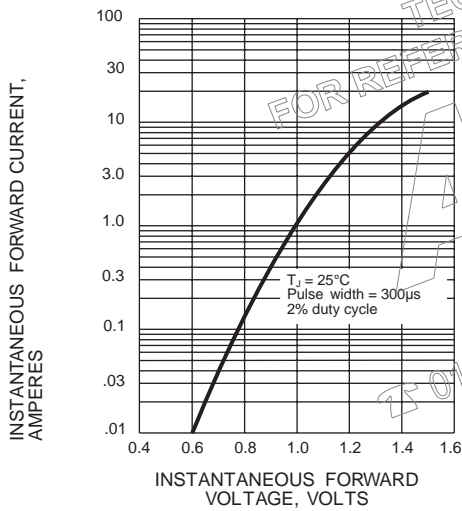


FIG. 4 - TYPICAL JUNCTION CAPACITANCE

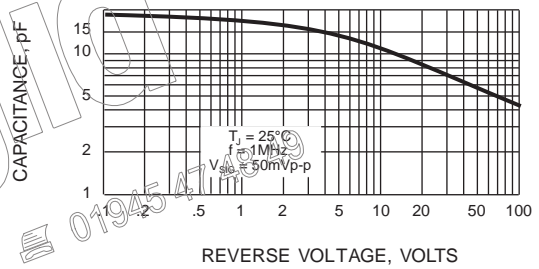
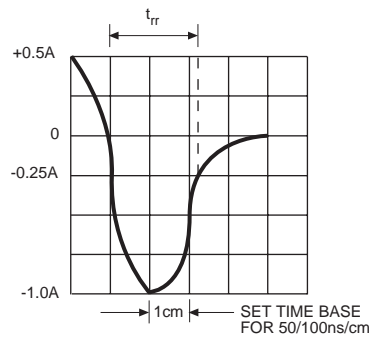
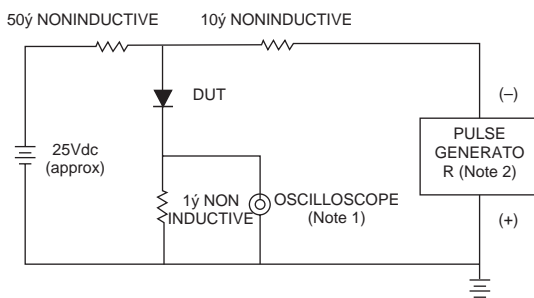


FIG. 5 - TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



- NOTES
- 1 Rise Time = 7ns max, Input Impedance = 1 megaohm 22pF
 - 2 Rise Time = 10ns max, Source Impedance = 50 ohms